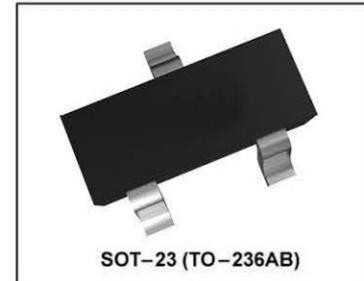
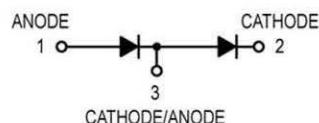


Dual Series Switching Diode

This switching diode has the following features:

- Low Leakage Current Applications
- Medium Speed Switching Times
- Available in 8 mm Tape and Reel



● MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	70	Vdc
Average Rectified Forward Current ⁽¹⁾ (averaged over any 20 ms period)	$I_{F(AV)}$	715	mAdc
Repetitive Peak Forward Current	I_{FRM}	450	mAdc
Non-Repetitive Peak Forward Current t = 1.0 μ s t = 1.0 ms t = 1.0 A	I_{FSM}	2.0 1.0 0.5	Adc

● THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ $T_A = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	P_D	225 1.8	mW mW/5C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	5C/W
Total Device Dissipation Alumina Substrate ⁽²⁾ $T_A = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	P_D	300 2.4	mW mW/5C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	5C/W
Junction and Storage Temperature	T_J, T_{stg}	-65 to +150	5C

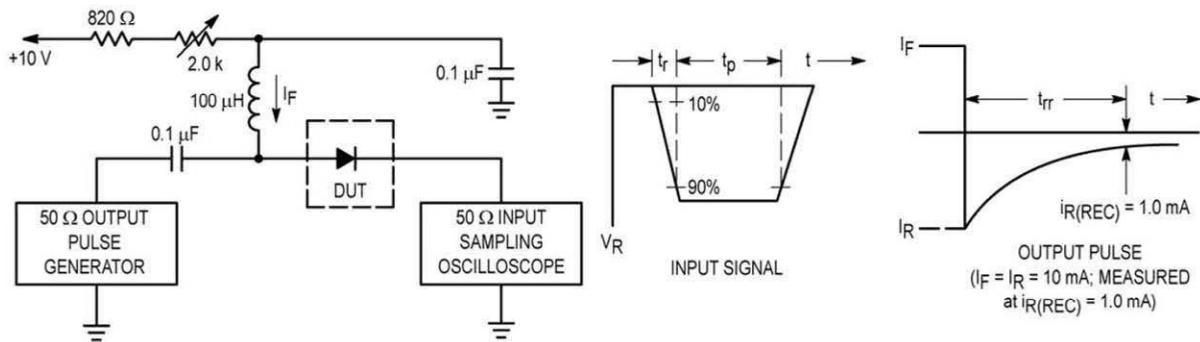
● DEVICE MARKING

BAV199= JY

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{Adc}$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ($V_R = 70 \text{ Vdc}$) ($V_R = 70 \text{ Vdc}, T_J = 150\text{C}$)	I_R	—	5.0 80	nAdc
Diode Capacitance ($V_R = 0 \text{ V}, f = 1.0 \text{ MHz}$)	C_D	—	2.0	pF
Forward Voltage ($I_F = 1.0 \text{ mAdc}$) ($I_F = 10 \text{ mAdc}$) ($I_F = 50 \text{ mAdc}$) ($I_F = 150 \text{ mAdc}$)	V_F	—	900 1000 1100 1250	mVdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}$) (Figure 1)	t_{rr}	—	3.0	μs


Figure 1. Recovery Time Equivalent Test Circuit